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Amorphous-Si, deposited using Dual-Frequency PECVD, at 300 C					
Pressure (mT)	2% SiH4 Flow-rate (sccm)	HF Power (W)	Deposition Rate* (nm/min)	Average Stress (MPa)	Pre-dep chamber Coating Time (min)
600	1500	30	6.65	-945	20

*: The rate was for the film deposited on 4" wafer (it was lowered for a smaller sample, like 10X10mm^2).

Figure 1 Amorphous-Si deposited on SiO_2 (~200nm)/Si substrate: a) Microscope picture; b) SEM picture.